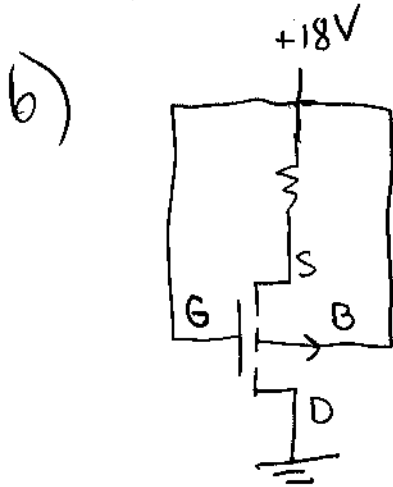
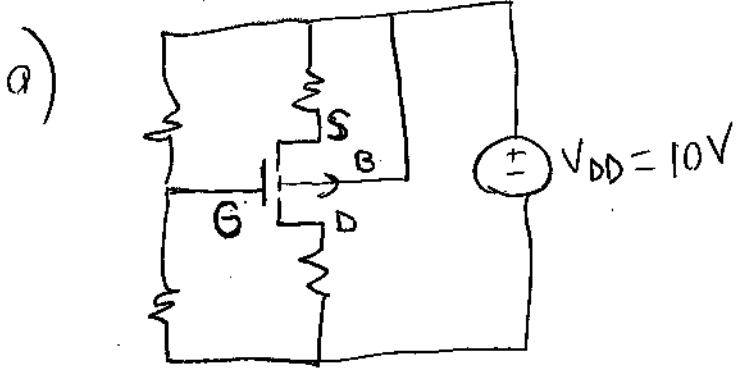
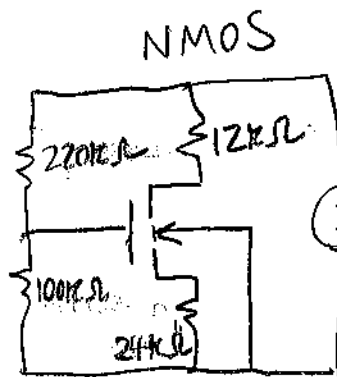


4.55

Arrow out means PMOS, so  $V_{DS} < 0$



4.93 part (a) only



$$V_T = 1V$$

$$\gamma = 0 \Rightarrow \text{No Body effect.}$$

$$K' = 100 \mu A/V^2$$

$$\frac{W}{L} = \frac{6}{1}$$

$$V_g = 10V \cdot \left( \frac{100k\Omega}{220k\Omega + 100k\Omega} \right) = 3.125V$$

- Assume Saturation region as initial guess.

$$I_D = \frac{1}{2} K' \frac{W}{L} (V_{gs} - V_T)^2 = 100 \mu A/V (6) (V_{gs} - V_T)^2$$

$$0 = 10V - I_D(24k\Omega) - V_{DS} - I_D(24k\Omega)$$

$$V_s = I_D(24k\Omega)$$

$$V_{gs} = 3.125V - I_D(24k\Omega)$$

$$I_D = \frac{1}{2} (100 \mu A/V^2) (6) (3.125V - I_D(24k\Omega) - 1V)^2$$

Solve for  $I_D$ ,  $I_D = 68.6 \mu A$  or  $1114 \mu A$

$$V_{gs} = 3.125V - (68.6 \mu A)(24k\Omega) = 1.48V$$

$$V_{DS} = 10V - (68.6 \mu A)(36k\Omega) = 7.53V$$

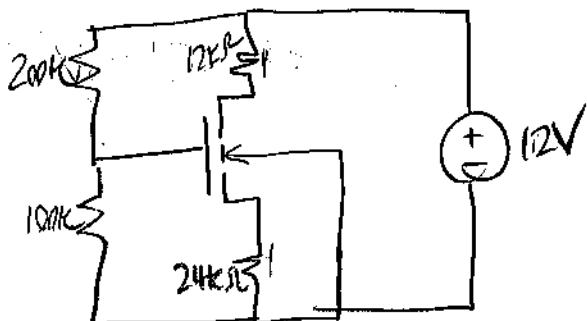
$$I_D = 68.6 \mu A$$

This current would give a  $V_{gs} < V_T$ , so it is not a physical answer

$V_{DS} > V_{gs} - V_T$ , so saturation assumption verified.

4.99

Hand calculation for  $V_{DS}=12V$ ,  $\frac{W}{L}=6$ ,



$$K' = 100 \mu A/V^2$$
$$\gamma = 0$$

$$V_G = 12V \left( \frac{100k\Omega}{220k\Omega + 100k\Omega} \right) = 3.75V$$

Assume Saturation

$$V_{GS} = 3.75V - I_D(12k\Omega)$$

$$V_{DS} = 12V - I_D(36k\Omega)$$

$$I_D = \frac{1}{2} (100 \mu A/V^2) (6) (3.75V - I_D(24k\Omega) - 1)^2$$

solve,  $I_D = 91.6 \mu A$  or  ~~$1143 \mu A$~~

→ Not physical  $V_{GS} < V_t$

$$V_{GS} = 3.75V - (91.6 \mu A)(24k\Omega) = 1.55V$$

$$V_{DS} = 12V - (91.6 \mu A)(36k\Omega) = 8.70V$$

$$I_D = 91.6 \mu A$$

$V_{DS} > V_{GS} - V_t$ , so saturation verified.

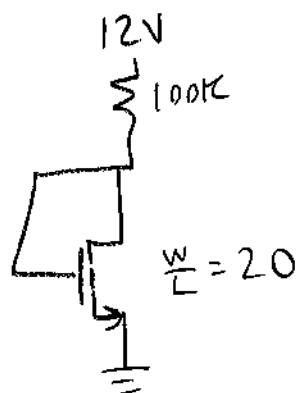
From Spice:

$$I_D = 91.6 \mu A, V_{DS} = 8.7V, V_{GS} = 1.55V$$

4.111

NMOS

a)



$$V_{GS} = 12V - I_D(100k\Omega)$$

$$V_{DS} = V_{GS} = 12V - I_D(100k\Omega)$$

$V_{DS} = V_{GS} > V_{GS} - V_T$ , therefore Saturation

$$K' = 100 \mu A/V^2, V_T = 0.75V$$

$$I_D = K' \frac{W}{L} (V_{GS} - V_T)^2$$

$$I_D = (100 \mu A/V^2)(20)(12V - I_D(100k\Omega) - 0.75V)^2$$

Solve for  $I_D$

$$I_D = 109 \mu A \text{ or } \cancel{110 \mu A}$$

$$V_{DS} = V_{GS} = 12V - (109 \mu A)(100k\Omega) = 1.08V$$

b) calculation same, except  $R = 330k\Omega$ .

$$I_D = (100 \mu A/V^2)(20)(12V - I_D(330k\Omega) - 0.75V)^2$$

$$I_D = 33.5 \mu A \text{ or } \cancel{34.7 \mu A}$$

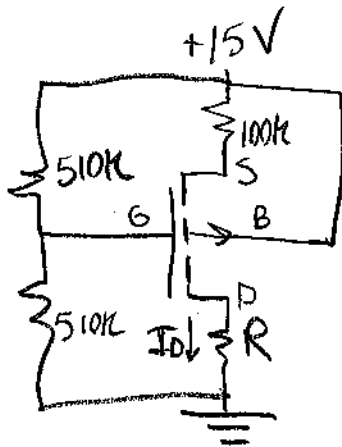
$$V_{DS} = V_{GS} = 12V - (33.7 \mu A)(330k\Omega) = 0.933V$$

Because  $I_g = 0A$ , the  $10M\Omega$  resistor doesn't matter.

4.138

PMOS

a)



$\gamma = 0, \Rightarrow$  No Body effect

$$\frac{W}{L} = 20$$

$$K' = 40 \mu A/V^2$$

$$V_{T0} = -0.75V$$

$$R = 50k\Omega$$

Assume saturation

$$V_g = 7.5V = 15V \frac{510k\Omega}{510k\Omega + 510k\Omega}$$

$$V_{DS} = -15V + I_D(100k\Omega + 50k\Omega)$$

$$V_{GS} = 7.5V - (15V - I_D(100k\Omega))$$

$$I_D = \frac{1}{2} (40 \mu A/V^2) (20) (7.5V - (15V - I_D(100k\Omega)) - (-0.75V))^2$$

Solve for  $I_D$ ,  $I_D = 63.5 \mu A$  or  ~~$110.7 \mu A$~~

$$V_{DS} = -5.47V$$

$$V_{GS} = -1.15V$$

$$I_D = 63.5 \mu A$$

$-V_{DS} > -(V_{GS} - V_T)$  so saturation is verified.

b) Solve for R w/  $V_{DS} = V_{GS} - V_T = -0.398V$  for maximum allowed R.

Note that in saturation,  $I_D$  is constant for  $\lambda = 0$ , so  $I_D$  is same as part (a)

$$V_{DS} = -15 + (100k\Omega + R)I_D$$

$$-0.398 = -15 + (100k\Omega + R)(63.5 \mu A)$$

$$R = 130k\Omega \text{ or less}$$

4.139

Hand calc:

$$\begin{cases} V_{DS} = -5.47V \\ V_{GS} = -1.15V \\ I_D = 63.5\mu A \end{cases}$$

Spice:

$$\begin{cases} I_D = 63.5\mu A \\ V_{DS} = -1.15V \\ V_{GS} = -5.47V \end{cases}$$

Compare these two results

5:9

Starting from eq. 5.13 in book...

$$I_C = I_E$$

$$V = V_{BE}$$

$$V_{BE} = 0V$$

$$I_E = I_s \left[ \exp\left(\frac{V_{BE}}{V_T}\right) - \exp\left(\frac{V_{BC}}{V_T}\right) \right] + \frac{I_s}{\beta_F} \left[ \exp\left(\frac{V_{BE}}{V_T}\right) - 1 \right]$$

$$I_E = I_s \left( \frac{\beta_F + 1}{\beta_F} \right) \left[ \exp\left(\frac{V_{BE}}{V_T}\right) - 1 \right]$$

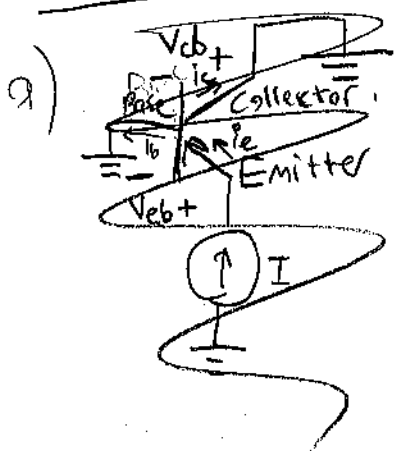
The transistor behaves like a diode with

$$I_{S \text{ Diode}} = I_s \left( \frac{\beta_F + 1}{\beta_F} \right)$$

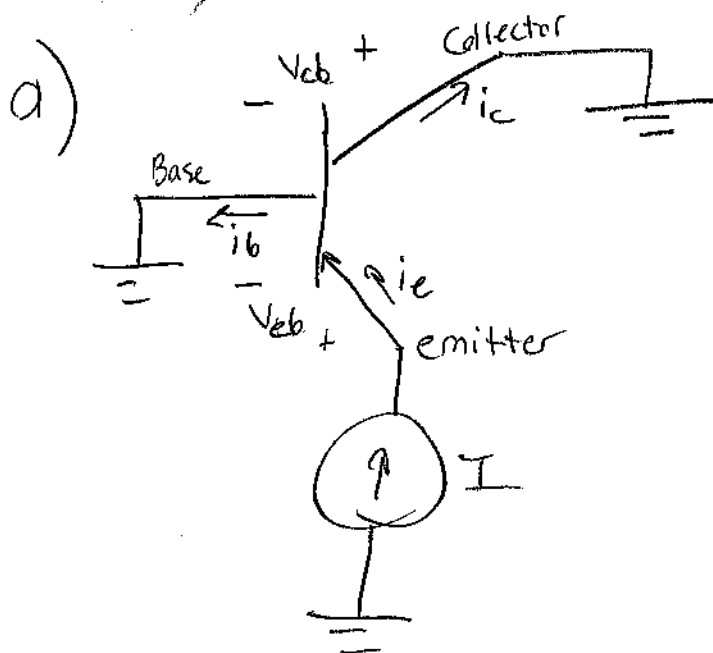
$$= 4 \times 10^{-15} \text{ A} \left( \frac{101}{100} \right)$$

$$I_{S \text{ Diode}} = 4.04 \times 10^{-15} \text{ A}$$

5.18



b) PNP BJT.



d)  $I = 300 \mu A = I_e$   $I_b = \frac{I_e}{\beta + 1}$

$$I_e = (\beta + 1) I_b \Rightarrow I_b = \frac{1}{\beta + 1} (I_e) = \frac{1}{101} 300 \mu A = 2.97 \mu A$$

$$I_c = \frac{\beta}{\beta + 1} I_e = \beta I_b = 297 \mu A$$

$$I_E = I_s \left( \exp\left(\frac{V_{EB}}{V_T}\right) - \exp\left(\frac{V_{CB}}{V_T}\right) \right) + \frac{I_s}{\beta_F} \left( \exp\left(\frac{V_{EB}}{V_T}\right) - 1 \right)$$

↑ because  $V_{CB} = 0V$

$$I_E = I_s \left( \frac{\beta_F + 1}{\beta_F} \right) \left( \exp\left(\frac{V_{EB}}{V_T}\right) + 1 \right)$$

$$300 \mu A = (5 \times 10^{-16} A) \left( \frac{101}{100} \right) \left( \exp\left(\frac{V_{EB}}{0.025V}\right) - 1 \right)$$

Solve,  $V_{EB} = 0.678 V$   $V_{CB} = 0 V$